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SEMICONDUCTOR



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PLED

74LVC1G34GW-MS/74LVC1G34GV-MS

Product specification

General Description

The operating voltage range of the 74LVC1G34GW-MS/74LVC1G34GV-MS single buffer is 1.65 V to 5.5V. The 74LVC1G34GW-MS/74LVC1G34GV-MS device contains one buffer and performs the Boolean function $Y = A$. The CMOS device has a high output drive while maintaining low static power dissipation over a broad VCC operating range.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

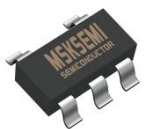
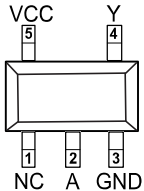
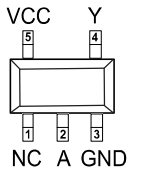
Features

- Low Power Consumption, 10- μ A Max I_{cc}
- Supports 5V VCC Operation
- Inputs Accept Voltages to 5.5V
- Max t_{pd} of 3.3 ns at 3.3 V
- ± 24 mA Output Drive at 3.3 V
- I_{off} Supports Partial-Power-Down Mode
- Typical $V_{OHV} > 2V$ at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$
- Typical $V_{OLP} < 0.8$ V at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$

Applications

- AV Receivers
- Audio Docks: Portable
- Blu-ray Players and Home Theater
- Embedded PC
- MP3 Player/Recorder (Portable Audio)
- Personal Digital Assistant (PDA)
- Power: Telecom/Server AC/DC Supply
- Solid State Drive (SSD): Client and Enterprise
- TV: LCD/Digital and High-Definition (HDTV)
- Tablet: Enterprise
- Video Analytics: Server
- Wireless Headset, Keyboard, and Mouse

Pinning and Marking

SOT-23-5	Pin Configurations	Marking	SOT-353	Pin Configurations	Marking
					

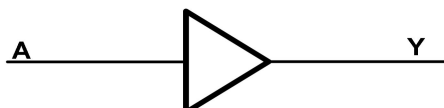
Pin Functions

Pin		Type	Description
Name	SOT23-5/SOT-353		
NC	1	—	No internal connection
A	2	I	Input
GND	3	—	Ground
Y	4	O	Output
VCC	5	—	Positive Supply

Order information

Orderable Device	Package	Packing Option
74LVC1G34GV-MS	SOT-23-5	3000PCS
74LVC1G34GW-MS	SOT-353	3000PCS

Circuit Diagram



Absolute Maximum Ratings

Parameters			Min	Max.	Unit
V _{CC}	Supply voltage range		-0.5	6.5	V
V _I	Input voltage range		-0.5	6.5	V
V _O	Voltage range applied to any output in the high-impedance or power-off state		-0.5	6.5	V
V _O	Voltage range applied to any output in the high or low state		-0.5	V _{CC} +0.5	V
I _K	Input clamp current	V _I <0		-50	mA
I _{OK}	Output clamp current	V _O <0		-50	mA
I _O	Continuous output current			±50	mA
Continuous current through V _{CC} or GND				±100	mA
T _J	Junction temperature under bias			150	°C
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply voltage		1.65	5.5	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	$V_{CC}=1.65\text{V}$		-4	mA
		$V_{CC}=2.3\text{V}$		-8	
		$V_{CC}=3\text{V}$		-16	
				-24	
		$V_{CC}=4.5\text{V}$		-32	
I_{OL}	Low-level output current	$V_{CC}=1.65\text{V}$		4	mA
		$V_{CC}=2.3\text{V}$		8	
		$V_{CC}=3\text{V}$		16	
				24	
		$V_{CC}=4.5\text{V}$		32	
T_A	Operating free-air temperature		-40	125	$^{\circ}\text{C}$

Electrical Characteristics

V_{CC}=5.0V or 3.3V, Typical values are at T_A =+25°C. (unless otherwise noted).

Parameter	Test Conditions	V _{CC}	-40°C to 85°C			-40°C to 125°C			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{OH}	I _{OH} =-100 μA	1.65 V to 5.5 V	V _{CC} -0.1			V _{CC} -0.1			V
	I _{OH} =-4 mA	1.65 V	1.2			1.2			
	I _{OH} =-8 mA	2.3 V	1.9			1.9			
	I _{OH} =-16 mA	3 V	2.4			2.4			
	I _{OH} =-24 mA		2.3			2.3			
	I _{OH} =-32 mA	4.5 V	3.8			3.8			
V _{OL}	I _{OL} =100 μA	1.65 V to 5.5 V			0.1			0.1	V
	I _{OL} =4 mA	1.65 V			0.45			0.45	
	I _{OL} =8 mA	2.3 V			0.3			0.3	
	I _{OL} =16 mA	3 V			0.4			0.4	
	I _{OL} =24 mA				0.55			0.55	
	I _{OL} =32 mA	4.5 V			0.55			0.55	
I _I	A input	V _I =5.5 V or GND			±5			±5	μA
I _{off}	V _I or V _O =5.5 V	0			±10			±10	μA
I _{CC}	V _I =5.5 V or GND, I _O =0	1.65 V to 5.5 V			10			10	μA
ΔI _{CC}	One input at V _{CC} -0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500			500	μA
C _i	V _I =V _{CC} or GND	3.3 V		5			5		pF

(1) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation

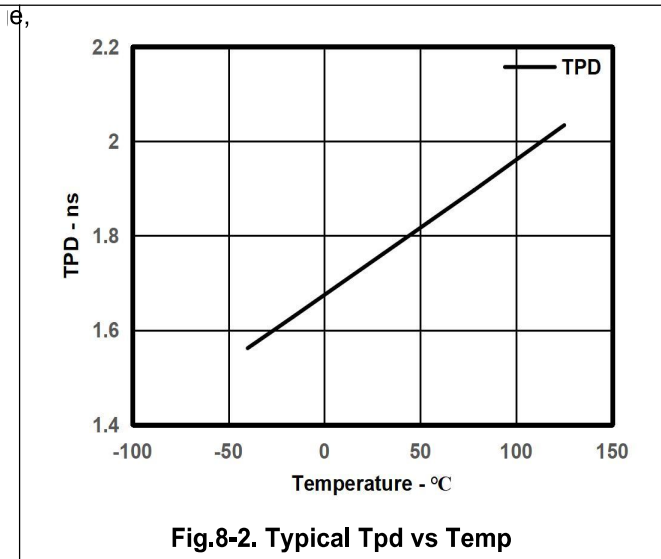
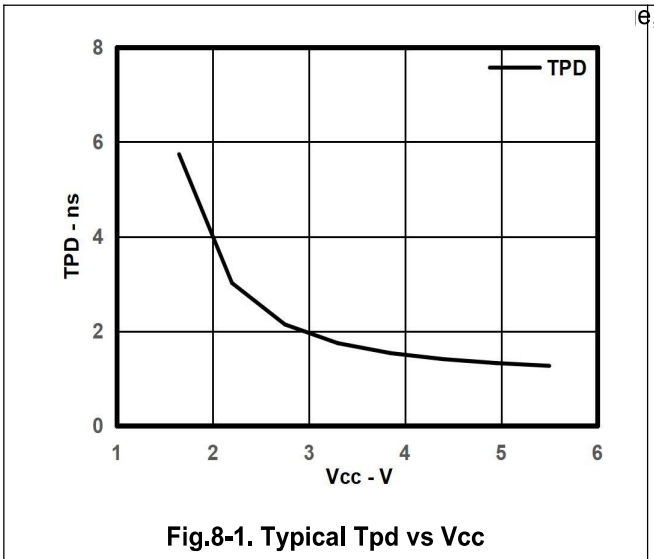
V_{CC}=5.0V or 3.3V, Typical values are at T_A =+25°C. (unless otherwise noted).

Parameter	From (Input)	To (Output)	-40°C to 125°C								Unit
			V _{CC} =1.8 V ± 0.15 V		V _{CC} =2.5 V ± 0.2 V		V _{CC} =3.3 V ± 0.3 V		V _{CC} =5 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	A	Y	3.9	9.5	1.4	4.5	1	3.3	1	3.0	ns

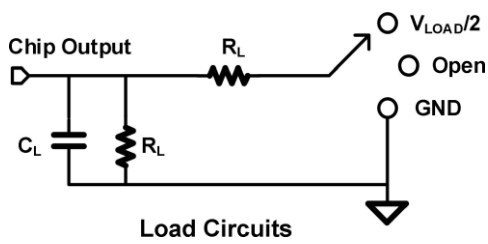
T_A=25°C

Parameter		Test Conditions	V _{CC} =1.8 V	V _{CC} =2.5 V	V _{CC} =3.3 V	V _{CC} =5 V	Unit
			Typ	Typ	Typ	Typ	
C _{pd}	Power dissipation capacitance	f=10 MHz	17	28	33	47	pF

Typical Characteristics



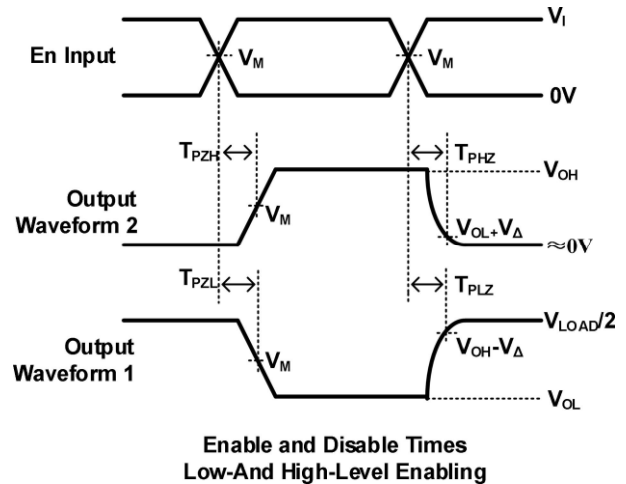
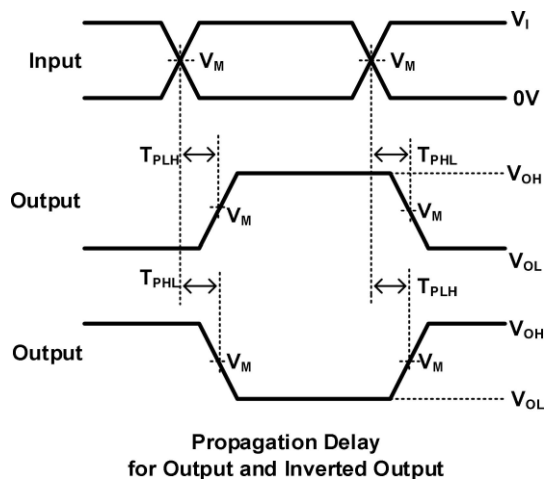
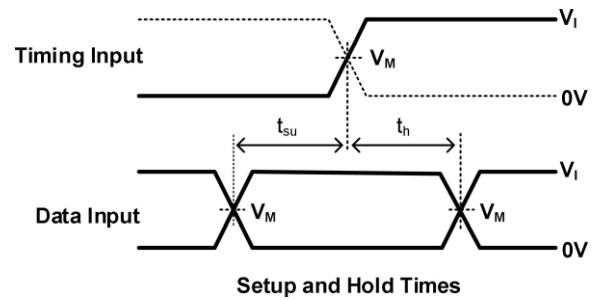
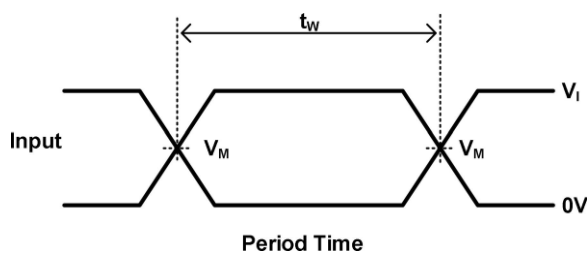
Parameter Measurement Information



TEST	S1
T_{PHL}/T_{PLH}	OPEN
T_{PLZ}/T_{PZL}	V_{LOAD}
T_{PHZ}/T_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	T_r/T_f					
$1.8V \pm 0.15V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	30pF	1k Ω	0.15V
$2.5V \pm 0.15V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	30pF	500 Ω	0.15V
$3.3V \pm 0.15V$	3V	$\leq 2.5ns$	1.5V	6V	50pF	500 Ω	0.3V
$5V \pm 0.15V$	V_{CC}	$\leq 2.5ns$	$V_{CC}/2$	$2 \times V_{CC}$	50pF	500 Ω	0.3V

Parameter Measurement Information(Continued)



Notes: A. C_L includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control.

Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR 10 MHz, $Z = 50$.

D. The outputs are measured one at a time, with one transition per measurement.

E. t_{PLZ} and t_{PHZ} are the same as t_{ds} .

F. t_{PZL} and t_{PZH} are the same as t_{en} .

G. t_{PLH} and t_{PHL} are the same as t_{pd} .

H. All parameters and waveforms are not applicable to all device.

Feature Description

The device is designed for 1.65V to 5.5V V_{CC} operation and it allows down voltage translation from 5V to 3.3V, or 3.3V to 1.8V. The input voltage of 74LVC1G34GW-MS/74LVC1G34GV-MS accepts to 5.5V.

The 74LVC1G34GW-MS/74LVC1G34GV-MS has power-down protection (off) and Schmitt-trigger input.

I_{off} feature allows voltage on the inputs and outputs when V_{CC} is 0V, and is able to reduce leakage when V_{CC} is 0V.

Schmitt-Trigger input can improve the noise immunity capability

Device Functional Modes

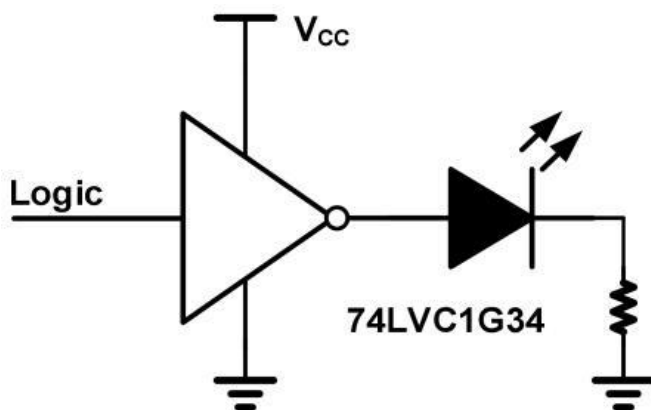
Input A	Output Y
H	H
L	L

Application Information

The 74LVC1G34GW-MS/74LVC1G34GV-MS is a high drive CMOS device that can be used for implementing inversion logic with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it ideal for driving multiple outputs and good for high-speed applications up to 100 Mhz.

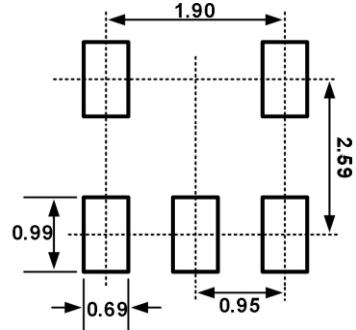
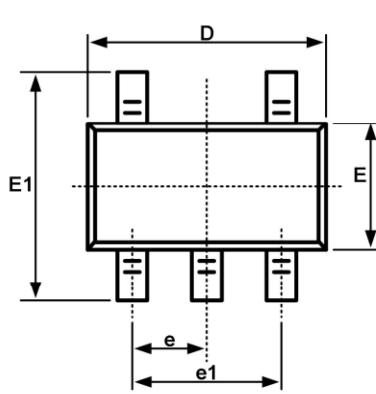
The inputs are 5.5 V tolerant allowing it to translate down to V_{CC} .

Typical Power Button Circuit

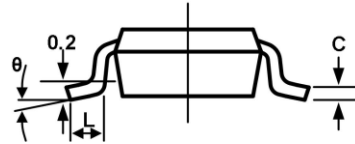
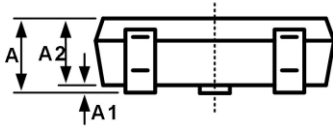


Package Outline

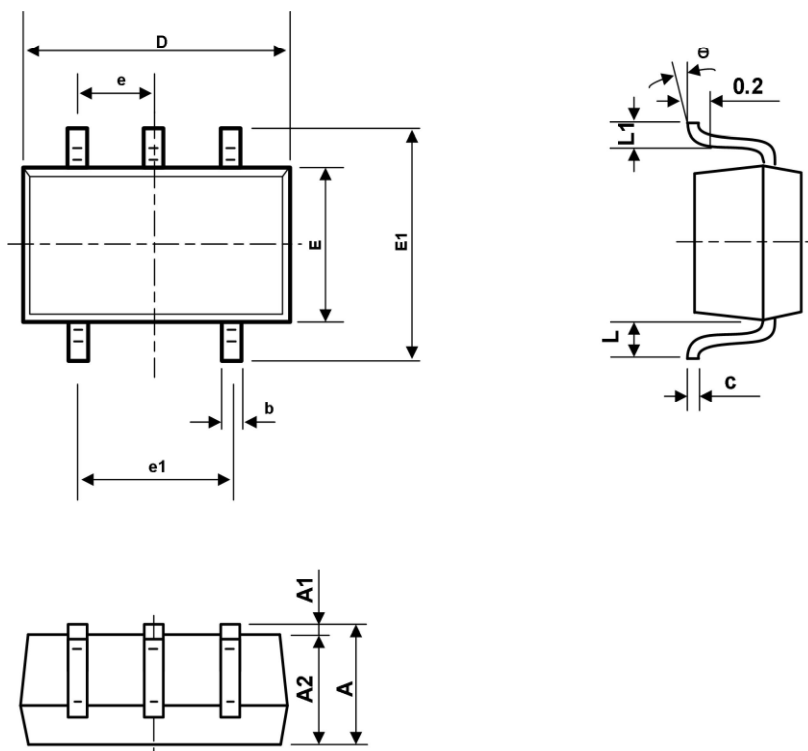
SOT23-5



Recommended Land Pattern (Unit: mm)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950BSC		0.037BSC	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
L1	0.600REF		0.024REF	
θ	0°	8°	0°	8°

Package Outline
SC70-5


symbol	Dimension In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.110	0.175	0.004	0.007
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

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